**Amendments to the Claims**:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of an alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, $0.001 \leq (A/Zn) \leq 500$.

2. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of Li and Zn, (Li/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, $0.001 \leq (Li/Zn) \leq 500$.

3. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of Na and Zn, (Na/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, $0.001 \leq (Na/Zn) \leq 100$.

4. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of K and Zn, (K/Zn), in a range from the surface of said element body to

a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, $0.001 \leq (K/Zn) \leq 100$.

5. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of Rb and Zn, (Rb /Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, $0.001 \leq (Rb/Zn) \leq 100$.

6. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of Cs and Zn, (Cs /Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, $0.001 \leq (Cs/Zn) \leq 100$.

7. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when measuring an ion intensity ratio of an alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of 100 μm by a secondary ion mass spectrometry, it is $0.001 \leq (A/Zn) \leq 500$.

8. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when measuring an ion intensity ratio of Li and Zn, (Li/Zn), in a range from the surface of said element body to a depth of 100 μm by a secondary ion mass spectrometry, it is $0.001 \leq (Li/Zn) \leq 500$.

9. (Original) The chip shaped electronic device as set forth in claim 8, wherein said ion intensity ratio is $0.01 \leq (Li/Zn) \leq 500$.

10. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when measuring an ion intensity ratio of Na and Zn, (Na/Zn), in a range from the surface of said element body to a depth of 100 μm by a secondary ion mass spectrometry, it is $0.001 \leq (Na/Zn) \leq 100$.

11. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when measuring an ion intensity ratio of K and Zn, (K/Zn), in a range from the surface of said element body to a depth of 100 μm by a secondary ion mass spectrometry, it is $0.001 \leq (K/Zn) \leq 100$.

12. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when measuring an ion intensity ratio of Rb and Zn, (Rb/Zn), in a range from the surface of said element body to a depth of 100 μm by a secondary ion mass spectrometry, it is $0.01 \leq (Rb/Zn) \leq 100$.

13. (Original) A chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, wherein

when measuring an ion intensity ratio of Cs and Zn, (Cs/Zn), in a range from the surface of said element body to a depth of 100 μm by a secondary ion mass spectrometry, it is $0.1 \leq (Cs/Zn) \leq 100$.

14. (Original) A chip shaped electronic device comprising:

an element body including zinc oxide material layers and internal electrode layers and having a size of 0.6 mm or less × 0.3 mm or less × a thickness of 0.3 mm or less; and

a pair of terminal electrodes formed on an outer surface of the element body, wherein a distance between facing end portions on the same plane (a gap between terminals) is 50 μm or more;

wherein when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of Li and Zn, (Li/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry (SIMS), it is 0.001

$\leq$ (Li/Zn) $\leq$ 500.

15. (Original) The chip shaped electronic device as set forth in claim 14, wherein said ion intensity ratio is 0.01 $\leq$ (Li/Zn) $\leq$ 500.

16. (Original) A chip shaped electronic device comprising:

an element body including zinc oxide material layers and internal electrode layers and having a size of 0.6 mm or less × 0.3 mm or less × a thickness of 0.3 mm or less; and

a pair of terminal electrodes formed on an outer surface of the element body, wherein a distance between facing end portions on the same plane is 50 μm or more;

wherein when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of Na and Zn, (Na/Zn), in a range from the surface of said element body to a depth of (0.9 × l) by a secondary ion mass spectrometry, it is 0.001 $\leq$ (Na/Zn) $\leq$ 100.

17. (Original) A chip shaped electronic device comprising:

an element body including zinc oxide material layers and internal electrode layers and having a size of 0.6 mm or less × 0.3 mm or less × a thickness of 0.3 mm or less; and

a pair of terminal electrodes formed on an outer surface of the element body, wherein a distance between facing end portions on the same plane is 50 μm or more;

wherein when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of K and Zn, (K/Zn), in a range from the surface of said element body to a depth of (0.9 × l) by a secondary ion mass spectrometry, it is 0.001 $\leq$ (K/Zn) $\leq$ 100.

18. (Original) A chip shaped electronic device comprising:

an element body including zinc oxide material layers and internal electrode layers and having a size of 0.6 mm or less × 0.3 mm or less × a thickness of 0.3 mm or less; and

a pair of terminal electrodes formed on an outer surface of the element body, wherein a distance between facing end portions on the same plane is 50 μm or more;

wherein when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of Rb and Zn, (Rb/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, it is $0.001 \leq (Rb/Zn) \leq 100$.

19. (Original) A chip shaped electronic device comprising:

an element body including zinc oxide material layers and internal electrode layers and having a size of 0.6 mm or less × 0.3 mm or less × a thickness of 0.3 mm or less; and

a pair of terminal electrodes formed on an outer surface of the element body, wherein a distance between facing end portions on the same plane is 50 μm or more;

wherein when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of Cs and Zn, (Cs/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, it is $0.001 \leq (Cs/Zn) \leq 100$.

20. (Original) A chip shaped electronic device comprising:

an element body including zinc oxide material layers and internal electrode layers and having a size of 0.6 mm or less × 0.3 mm or less × a thickness of 0.3 mm or less; and

a pair of terminal electrodes formed on an outer surface of the element body, wherein a distance between facing end portions on the same plane is 50 μm or more;

wherein when assuming a minimum distance from an outermost side of said internal electrode layer in the stacking direction to a surface of said element body is l and measuring an ion intensity ratio of an alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry, it is $0.001 \leq (A/Zn) \leq 500$.

21. (Currently Amended) The chip shaped electronic device as set forth in ~~any one of claims 1 to 20,~~ claim 1, wherein said element body has the configuration of alternately stacking zinc oxide voltage nonlinear resistor layers and internal electrode layers, and said chip shaped electronic device is a multilayer type chip varistor.

22. (Original) A method of producing a chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, and a pair of terminal electrodes formed on an outer surface of the element body, including the steps of:

forming said element body;

diffusing an alkali metal (A) from a surface of said element body to inside the element body; and

after that, forming on the outer surface of said element body said pair of terminal electrodes connected to said internal electrode layers;

wherein:

the alkali metal is diffused under a condition of attaining $0.001 \leq (A/Zn) \leq 500$ when assuming a minimum distance from an outermost layer side of said internal electrode layers in the stacking direction to the surface of said element body is l at the time of diffusing said alkali metal and measuring an ion intensity ratio of the alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry.

23. (Original) A method of producing a chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, and a pair of terminal electrodes formed on an outer surface of the element body, including the steps of:

forming said element body;

forming on the outer surface of said element body terminal electrodes connected to said internal electrode layers; and

after that, diffusing an alkali metal (A) from a surface of said element body to inside the element body;

wherein:

the alkali metal is diffused under a condition of attaining $0.001 \leq (A/Zn) \leq 500$

when assuming a minimum distance from an outermost layer side of said internal electrode layers in the stacking direction to the surface of said element body is l at the time of diffusing said alkali metal and measuring an ion intensity ratio of the alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry.

24. (Original) A method of producing a chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, including the steps of:

forming said element body;

diffusing an alkali metal (A) from a surface of said element body to inside the element body; and

after that, forming on the outer surface of said element body terminal electrodes connected to said internal electrode layers; and

wherein:

the alkali metal is diffused under a condition of attaining $0.001 \leq (A/Zn) \leq 500$ when measuring an ion intensity ratio of the alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of 100 μm by a secondary ion mass spectrometry.

25. (Original) A method of producing a chip shaped electronic device comprising an element body including zinc oxide material layers and internal electrode layers, including the steps of:

forming said element body;

forming on the outer surface of said element body terminal electrodes connected to said internal electrode layers; and

after that, diffusing an alkali metal (A) from a surface of said element body to inside the element body;

wherein:

the alkali metal is diffused under a condition of attaining $0.001 \leq (A/Zn) \leq 500$ when measuring an ion intensity ratio of the alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of 100 μm by a secondary ion mass spectrometry.

26. (Original) A method of producing a chip shaped electronic device comprising:

an element body including zinc oxide material layers and internal electrode layers and having a size of 0.6 mm or less × 0.3 mm or less × a thickness of 0.3 mm or less; and

a pair of terminal electrodes formed on an outer surface of the element body, wherein a distance between facing end portions on the same plane is 50 μm or more; including the steps of:

forming said element body;

diffusing an alkali metal (A) from a surface of said element body to inside the element body; and

after that, forming on the outer surface of said element body said pair of terminal electrodes connected to said internal electrode layers;

wherein:

the alkali metal is diffused under a condition of attaining $0.001 \leq (A/Zn) \leq 500$ when assuming a minimum distance from an outermost layer side of said internal electrode layers in the stacking direction to the surface of said element body is l at the time of diffusing said alkali metal and measuring an ion intensity ratio of the alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry.

27. (Original) A method of producing a chip shaped electronic device comprising:

an element body including zinc oxide material layers and internal electrode layers and having a size of 0.6 mm or less × 0.3 mm or less × a thickness of 0.3 mm or less; and

a pair of terminal electrodes formed on an outer surface of the element body, wherein a distance between facing end portions on the same plane is 50 μm or more; including the steps of:

forming said element body;

forming on the outer surface of said element body said pair of terminal electrodes connected to said internal electrode layers; and

after that, diffusing an alkali metal (A) from a surface of said element body to inside the element body;

wherein:

the alkali metal is diffused under a condition of attaining $0.001 \leq (A/Zn) \leq 500$ when assuming a minimum distance from an outermost layer side of said internal electrode layers in the stacking direction to the surface of said element body is l at the time of diffusing said alkali metal and measuring an ion intensity ratio of the alkali metal (A) and zinc (Zn), (A/Zn), in a range from the surface of said element body to a depth of $(0.9 \times l)$ by a secondary ion mass spectrometry.

28. (Currently Amended) The chip shaped electronic device as set forth in ~~any one of claims 22 to 27,~~ claim 22,. wherein said alkali metal is at least one of Li, Na, K, Rb and Cs.

29. The chip shaped electronic device as set forth in ~~any one of claims 22 to 27,~~ claim 22, wherein at the time of diffusing said alkali metal, said element body is subjected to heat treatment at a temperature of 700 to 1000°C in a state of being applied with powder of an alkali metal compound, and at least one of an application amount of said powder to the surface of said element body, a heat treatment temperature and a heat treatment time is controlled.